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# Investigation of Switching Oscillations for Silicon Carbide MOSFETs in Three-Level Active Neutral-Point-Clamped Inverters

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**Abstract**—This paper investigates the multi-frequency switching oscillations of silicon carbide (SiC) MOSFETs in three-level active neutral-point-clamped (3L-ANPC) inverters under three typical commutation modes (i.e., the full mode, outer mode, and inner mode). Multiple switching-oscillation components with various frequencies are identified theoretically for both the full-mode and outer-mode commutations, due to their switching-loop diversities. Oppositely, the inner mode exhibits a single oscillation component as only one switching loop is involved. Three types of double-pulse tests (DPTs) are conducted on a 3L-ANPC inverter demonstrator with SiC MOSFETs, and the switching-oscillation components are extracted accordingly, which match well with the theoretical derivations. Moreover, other switching characteristics closely related, i.e., the oscillation peaks, current overshoots, capacitive charges, and switching energies, are studied and benchmarked according to the DPT results. It is concluded that the full-mode and outer-mode commutations share similarities in terms of switching oscillations, current overshoots, capacitive charges, and turn-on energies. The theoretical findings from this work provide a comprehensive knowledge of the multi-frequency oscillation mechanisms associated with fast-switched 3L-ANPC inverters. Accordingly, the critical parasitic-components are identified, and specific design considerations are proposed to achieve switching-performance improvements.

**Index Terms**—Active neutral-point-clamped (ANPC) inverter, double pulse test (DPT), multi-frequency switching oscillation, silicon carbide (SiC) MOSFET, switching loops.

## I. INTRODUCTION

OVER the past decade, the evolution of power electronic converter has been extensively driven by semiconductor devices manufactured by wide bandgap (WBG) materials [1]–[3], i.e., the gallium nitride (GaN) and silicon carbide (SiC) [4]. One of the most popular WBG devices is the SiC MOSFET, as it nicely fits into the need of 1.2–3.3 kV blocking voltage in numerous applications, e.g., grid-connected inverters [5], uninterruptible power supplies [6], [7], railway traction converters [8], and electric vehicles [9], [10].

As a WBG device, the SiC MOSFET features several superiorities in comparison with the silicon (Si) IGBT, e.g.,

high-temperature operation capability [4], enhanced electric field [11], and compact die area. More importantly, the faster switching speed, as well as the strengthened  $dv/dt$  and  $di/dt$  capabilities, are achievable by using the SiC MOSFET [3]. However, the increasing switching speed poses new challenges from the following perspectives: a) the robustness margin shall be ensured in terms of the overvoltage and gate-oxide failures [12]; b) the electro-magnetic interference (EMI) filters should be properly sized and optimized to cope with more switching noises [7], [13]; c) the circuit layout becomes more critical in order to fully utilize the switching capabilities of SiC MOSFETs. Hence, the switching characterization becomes essential for the performance evolution and design iteration of the SiC MOSFET based power electronic converters.

The switching behaviors of SiC MOSFETs in discrete-devices and half-bridge circuits have been intensively discussed in prior-art [14]–[22]. The experimental methodologies for switching characterization of SiC MOSFET were introduced in [14], [15]. The switching performance of a discrete SiC MOSFET was evaluated in [16], and these SiC switching characteristics in half-bridge circuits were assessed in [17]–[19]. Furthermore, theoretical models have been developed for the switching-behavior predictions [20]–[22]. A loss model of SiC MOSFET was proposed in [20] for high-frequency applications. The switching oscillation of SiC MOSFET was modeled and analyzed in [21], [22]. Nevertheless, the above-mentioned studies focus on discrete-devices or half-bridge circuits, and their conclusions may not be directly applicable to three-level (3L) converters. The line-frequency devices in 3L converters can introduce extra switching loops, which may affect switching behaviors such as commutation losses, device stresses, and switching oscillations.

In recent years, the three-level active neutral-point-clamped (3L-ANPC) inverter has become an active and important research topic, as it can actively re-shape the loss and thermal distributions among power semiconductors by manipulating ANPC commutation modes [23]–[27]. Three typical commutation modes (i.e., the full mode, outer mode, and inner mode) for the 3L-ANPC inverter were first introduced in [24]. The conventional switching loops and switching behaviors associated with the three commutation modes were studied in [26], [27], which were based on a Si-IGBT switched 3L-ANPC inverter. Recently, the applications of SiC MOSFETs in 3L-ANPC inverters have been reported in literatures with performance improvements [28]–[34], and more characteristics

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regarding the switching behavior of SiC MOSFETs were explored in [35]–[39]. Specifically, the extra junction capacitance and the secondary switching loop introduced by line-frequency devices in 3L-ANPC inverters were identified in [36] under both the outer and inner commutations. Due to the multiple switching loops and high  $dv/dt$  and  $di/dt$ , the commutation of SiC MOSFET in 3L-ANPC inverters introduces multiple switching-oscillation components, which engender voltage overshoots during switching transients. Additionally, these oscillation components with different frequencies can significantly deteriorate the EMI performance.

In literature [37], the multi-switching loop induced over-voltage issues on line-frequency switches (under both the outer and inner commutations) were introduced. Furthermore, an analytical model for these multi-switching loop induced voltage overshoots in 3L-ANPC inverters was established in [38], which focuses on the outer-mode commutation. To reduce these risky voltage overshoots, a layout-optimized busbar design and a control method were proposed in [39] and [40], respectively. However, the aforementioned studies did not provide knowledge regarding the multi-frequency switching oscillations associated with the 3L-ANPC inverter. References [36]–[40] concentrate on the over-voltage amplitudes of switches and their mitigation methods, while the investigation of switching oscillations from a frequency perspective is still missing. Moreover, as the distributions of these oscillation frequencies are intensively dependent on the commutation modes, a comprehensive understanding of the multi-frequency mechanisms is highly demanded for a reliable and low-EMI operation of the 3L-ANPC inverter with SiC MOSFETs.

The key contribution of this paper focuses on studying the multi-frequency switching oscillations of SiC MOSFETs under the three representative ANPC commutation modes. A SiC MOSFET module and a 3L-ANPC inverter phase-leg are introduced in Section II. A simplified parasitic model of the 3L-ANPC phase-leg is developed based on finite-element method (FEM) simulations. Then, the three 3L-ANPC commutation modes and their equivalent switching circuits are discussed in Section III, and multiple switching-oscillation components are identified accordingly. Specific double pulse test (DPT) configurations are discussed in Section IV, and the DPT waveforms under the three commutation modes are presented. Then, the switching-oscillation components extracted from DPT waveforms, i.e., the experimental frequency-spectrum, are discussed in Section V, and the theoretical derivations of switching oscillations are validated under each 3L-ANPC commutation mode. Other switching characteristics closely related, i.e., oscillation peaks, current overshoots, capacitive charges, and switching energies, are studied and benchmarked in Section VI. Additionally, specific design considerations are proposed to achieve performance improvements. Finally, conclusions are drawn in Section VII.

## II. PARASITIC MODEL OF 3L-ANPC PHASE-LEG WITH SiC MOSFET MODULES

### A. SiC MOSFET Module

Contemporarily, the SiC MOSFET modules are under intensive development; however, the commercial SiC-based 3L-

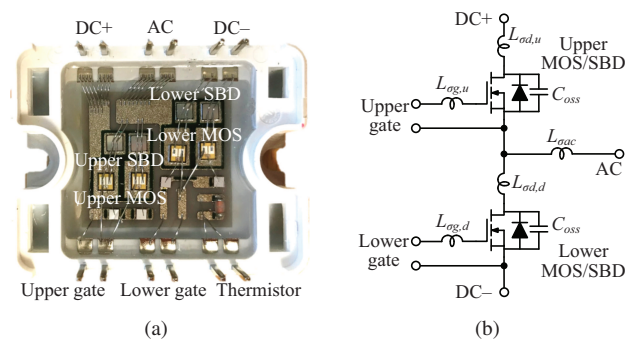


Fig. 1. Top view and circuit diagram of the SiC half-bridge module APTMC120AM55CT1AG from Microsemi. (a) Top view. (b) Module-level circuit diagram.

TABLE I  
EXTRACTED PARASITIC INDUCTANCES AND RESISTANCES OF THE SiC HALF BRIDGE MODULE. (OBTAINED AT 1 MHz)

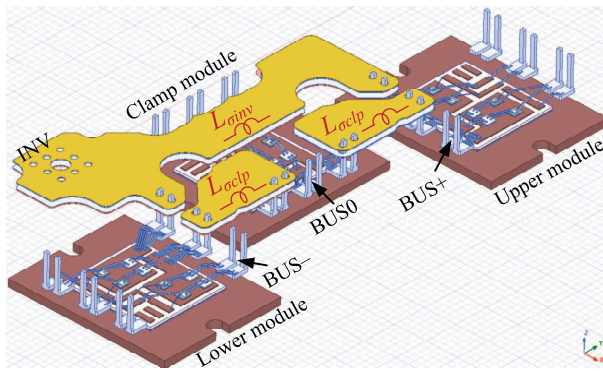
| Category     | Symbol           | Inductance (nH)  | Resistance (mΩ) |
|--------------|------------------|------------------|-----------------|
| AC terminal  | $L_{\sigma ac}$  | 6.0              | 1.0             |
| Upper device | gate             | $L_{\sigma g,u}$ | 9.4             |
|              | drain+source     | $L_{\sigma d,u}$ | 10.0            |
| Lower device | gate             | $L_{\sigma g,d}$ | 12.0            |
|              | drain+source     | $L_{\sigma d,d}$ | 12.9            |
| PCB trace    | $L_{\sigma clp}$ | 5.2              | 1.0             |
|              | $L_{\sigma inv}$ | 34.1             | 5.6             |
| Busbar       | $L_{\sigma bus}$ | 3.6              | —               |

ANPC module is rarely available in the market. The half-bridge SiC module APTMC120AM55CT1AG from Microsemi is adopted as the building block of the 3L-ANPC phase-leg. The device is rated at 1200 V and 42 A [41]. As demonstrated in Fig. 1(a), the half-bridge module contains two pairs of SiC MOSFET die with the reverse SiC Schottky barrier diode (SBD) die, which are symbolized as the upper and lower MOS/SBDs in Fig. 1(b), respectively.

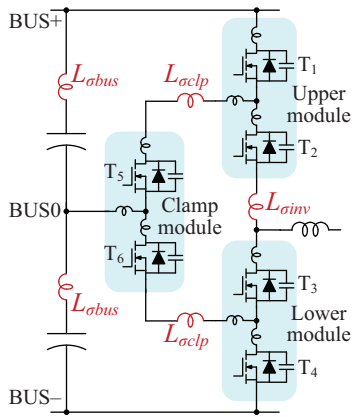
In order to interconnect the dies with the power terminals, bond wires and copper planes are applied in the SiC MOSFET module, which inevitably introduces parasitic inductances and alters the switching characteristics to some extent. FEM simulations (ANSYS/Q3D) are performed to extract the parasitic inductances of the half-bridge module. As illustrated in Fig. 1(b),  $L_{\sigma g,x}$  ( $x = u$  or  $d$ ) and  $L_{\sigma ac}$  stand for the parasitic inductor located at the gate and ac terminals, respectively. The parasitic inductors introduced by drain and source connections are simplified as a single component  $L_{\sigma d,x}$  ( $x = u$  or  $d$ ). The inductance values joint with their series resistances measured at 1 MHz are summarized in Table I. Various inductance values are identified, and they are dependent on geometries of the conductors.

### B. 3L-ANPC Phase-Leg

As shown in Figs. 2(a) and 2(b), the ANPC phase-leg is assembled by three aforementioned half-bridge modules, which are denoted as the upper module, clamp module, and lower module, respectively. Doing so, the ANPC phase-leg is capable



(a)



(b)

Fig. 2. Physical layout and simplified parasitic model of the 3L-ANPC phase-leg. (a) Physical layout. (b) Circuit diagram of the simplified parasitic model including parasitic inductances induced by both the module packaging and PCB traces.

of bearing a dc-bus voltage of 1500 V. A four-layer printed circuit board (PCB) is designed to interconnect the three half-bridge modules. It also introduces unavoidable routing inductances to the switching loop, although special efforts have been taken to minimize the loop areas.

The variables of  $L_{\sigma clp}$  and  $L_{\sigma inv}$  represent the PCB routing inductances of the neutral-tap connection and ac output connection, respectively. These PCB induced parameters are also obtained by FEM simulations, which are illustrated in Table I. It is noted that the neutral-tap inductance  $L_{\sigma clp}$  (5.2 nH) is comparable with the ones caused by the module packaging, while the inductance  $L_{\sigma inv}$  (34.1 nH) is relatively higher due to its unique geometry.

### C. PCB Busbar and Hybrid Capacitor Bank

The dc rails of the 3L-ANPC phase-leg, i.e., BUS+, BUS0, and BUS-, are connected to the top layer, the dual-mid layers, and the bottom layer of the four-layer PCB busbar, respectively. Moreover, a 1500-V hybrid capacitor bank with both aluminum electrolytic capacitors (Al-Caps) and metalized polypropylene film capacitors (MPPF-Caps) is implemented [42].

It is noted that the capacitor's equivalent-series-inductance (ESL) and busbar routing inductance should also be counted

TABLE II  
SWITCHING STATES OF THE 3L-ANPC PHASE-LEG [24].

| States | T <sub>1</sub> | T <sub>2</sub> | T <sub>3</sub> | T <sub>4</sub> | T <sub>5</sub> | T <sub>6</sub> |
|--------|----------------|----------------|----------------|----------------|----------------|----------------|
| -      | 0              | 0              | 1              | 1              | 1              | 0              |
| OL2    | 0              | 0              | 1              | 0              | 0              | 1              |
| OL1    | 1              | 0              | 1              | 0              | 0              | 1              |
| OF     | 0              | 1              | 1              | 0              | 1              | 1              |
| OU1    | 0              | 1              | 0              | 1              | 1              | 0              |
| OU2    | 0              | 1              | 0              | 0              | 1              | 0              |
| +      | 1              | 1              | 0              | 0              | 0              | 1              |

into the switching loop. In order to minimize the routing inductance, the PCB layer stack is designed to have the maximum overlap, and the technique of magnetic-field cancellation is utilized for the capacitor-bank layout [43]. Furthermore, external snubber capacitors with superior high-frequency performance are embedded. Overall, the capacitor-bank ESL joint with the routing inductance is estimated to be 3.6 nH, which is simplified as the single busbar inductance  $L_{\sigma bus}$ .

### III. INVESTIGATIONS OF SWITCHING OSCILLATIONS OF THE 3L-ANPC PHASE-LEG

In this section, the switching oscillations of the 3L-ANPC phase-leg under the full-mode, outer-mode, and inner-mode commutations are investigated. The 3L-ANPC switching states will be introduced first, as listed in Table II [24].

During the “-” state, both switches T<sub>3</sub> and T<sub>4</sub> are turned on to conduct the load current to the negative bus rail. Meanwhile, the switch T<sub>5</sub> is turned on to equalize the voltage stress between switches T<sub>1</sub> and T<sub>2</sub>. Analogously, during the “+” state T<sub>1</sub> and T<sub>2</sub> conduct the load current to the positive bus rail, and switch T<sub>6</sub> is utilized to equalize the voltage stress between T<sub>3</sub> and T<sub>4</sub>. Besides, by turning on T<sub>3</sub> and T<sub>6</sub>, the load current is conducted through the lower neutral path in both directions; meanwhile, T<sub>1</sub> can be in either OFF or ON state, resulting in two switching states “OL2” and “OL1”, respectively. Similarly, the load current is conducted through the upper path of the neutral path if both T<sub>2</sub> and T<sub>5</sub> are turned on, and T<sub>4</sub> can be in either OFF or ON state, which determines the two switching states “OU2” and “OU1”, respectively. In order to diminish the conduction loss, the load current can also conduct through both the upper and lower paths of the neutral tap by turning on T<sub>2</sub>, T<sub>3</sub>, T<sub>5</sub>, and T<sub>6</sub> simultaneously. This pattern is noted as the full-clamping state “OF”.

Therefore, multiple possibilities of commutations could happen between one of the active states (“-” and “+”) and one of the clamping states (“OL2”, “OL1”, “OU1”, “OU2”, and “OF”), which leads to several different 3L-ANPC commutation modes. Without losing its generality, the switching-oscillation mechanisms of three representative commutation modes, i.e., the full mode, outer mode, and inner mode, will be illustrated in the following sub-sections.

#### A. Full-Mode Commutation (“- ↔ OF” and “+ ↔ OF”)

The full-mode commutation was first indicated in [24], and further studied in [27], [28]. Transitions “- ↔ OF” and

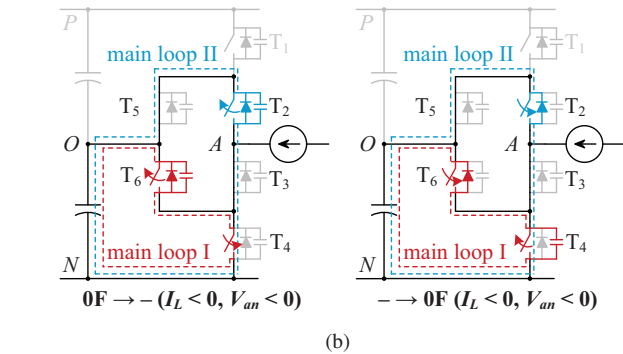
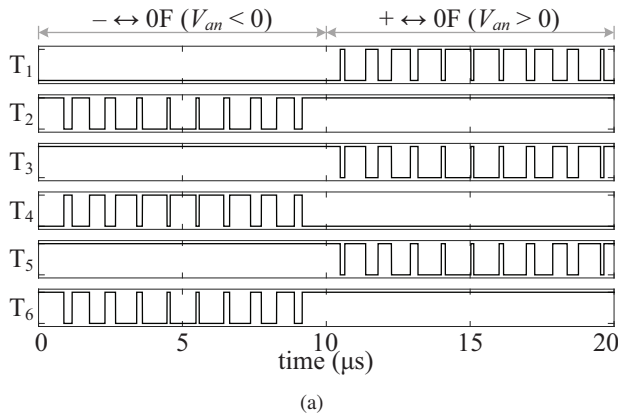


Fig. 3. Full-mode commutation of the 3L-ANPC phase-leg. (a) Gating signals. (b) Circuit diagrams during transitions “0F → -” and “- → 0F”.

“+ ↔ 0F” are achieved during the negative and positive cycles, respectively. Both the upper and lower paths of the neutral tap conduct during the clamping state “0F”, which is accomplished by turning on switches  $T_2$ ,  $T_3$ ,  $T_5$ , and  $T_6$  simultaneously. The gating signals and circuit diagrams of the full-mode commutation are depicted in Figs. 3(a) and 3(b) respectively. For simplification, only the operating principle during the negative cycle is elaborated. As demonstrated in Fig. 3(a), the outer switch  $T_4$  is switched to be sinusoidal during the negative cycle. Meantime,  $T_2$  and  $T_6$  share identical switching signals, which operate complementarily with  $T_4$ . The load current commutates between the active phase arm and both the upper and lower neutral paths. As a result, the full-mode commutation involves dual switching loops, as they are indicated as the main loop I and main loop II in Fig. 3(b).

The equivalent switching circuits for transitions “0F → -” and “- → 0F” are illustrated in Figs. 4(a) and 4(b), respectively.  $L_{lpx}$  and  $R_{lpx}$  ( $x = 1$  or  $2$ ) denote the inductance and resistance of the switching loop  $x$ . Additionally,  $L_{cm}$  and  $R_{cm}$  are the common inductance and resistance shared by the main loops I and II, and  $R_{on}$  denotes the on-state resistance of the SiC MOSFET. These parameters are listed in Table III, which are obtained according to the parasitic model studied in Section II. It is noted that the loop inductance and resistance of loop II (i.e.,  $L_{lp2}$  and  $R_{lp2}$ ) are significantly larger than those of the loop I (i.e.,  $L_{lp1}$  and  $R_{lp1}$ ) owing to the difference in loop length.

During the turn-on transient of  $T_4$  (i.e., the transition “0F → -”), the output capacitors of  $T_6$  and  $T_2$  are charged through

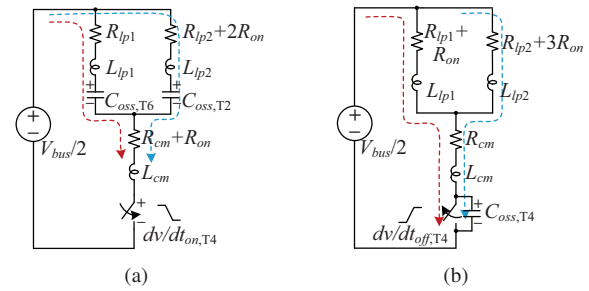


Fig. 4. Equivalent switching circuits of the full-mode commutation. (a) Equivalent switching circuit during transition “0F → -”. (b) Equivalent switching circuit during transition “- → 0F”.

TABLE III  
SWITCHING-LOOP ASSOCIATED PARASITIC PARAMETERS EXTRACTED FROM ANSYS/Q3D.

| Symbol                     | Inductance (nH) | Resistance (mΩ) | Capacitance (pF) |
|----------------------------|-----------------|-----------------|------------------|
| $L_{lp1}$ , $R_{lp1}$      | 24.1            | 5.8             | -                |
| $L_{lp2}$ , $R_{lp2}$      | 78.2            | 18.8            | -                |
| $L_{lp3}$ , $R_{lp3}$      | 40.8            | 10.4            | -                |
| $L_{cm}$ , $R_{cm}$        | 22.5            | 4.8             | -                |
| $R_{on}$                   | -               | 49              | -                |
| $C_{oss,Tx}$ ( $x = 1-6$ ) | -               | -               | 270 @ 500 V      |

loops I and II, respectively, as it is illustrated in Fig. 4(a). Therefore, the capacitive current flowing through  $T_4$  contains both these through  $C_{oss,T6}$  and  $C_{oss,T2}$ . Moreover, a dual-frequency oscillation shall be incurred due to the multiple switching loops. The impedance curve of the equivalent switching circuit during the transition “0F → -” is exhibited in Fig. 5(a). Two oscillation frequencies of 29.4 MHz and 49.4 MHz can be identified, which are dominated by loop II and loop I, respectively. Theoretically, the two oscillation frequencies of  $f_{osc1}^{0F \rightarrow -}$  and  $f_{osc2}^{0F \rightarrow -}$  can be obtained by letting the imaginary part of the total impedance to be zero:

$$f_{osc1,osc2}^{0F \rightarrow -} = \frac{1}{2\pi} \cdot \sqrt{\frac{L_{lp1} + L_{lp2} + 2L_{cm} \pm \sqrt{(L_{lp1} - L_{lp2})^2 + (2L_{cm})^2}}{2C_{oss} \cdot (L_{lp1}L_{lp2} + L_{lp1}L_{cm} + L_{lp2}L_{cm})}} \quad (1)$$

where  $C_{oss}$  denotes the device output capacitance with drain-source voltage being 500 V, which equals to 270 pF in this work.

During the turn-off transient of  $T_4$  (i.e., the transition “- → 0F”), the output capacitance of  $T_4$  (i.e.,  $C_{oss,T4}$ ) is charged by one part of the load current, while both  $C_{oss,T2}$  and  $C_{oss,T6}$  are discharged through the other part of load current, simultaneously. After the drain-source voltage of  $T_4$  reaches  $V_{bus}/2$  and the phase current is fully transferred to  $T_2$  and  $T_6$ , the switching oscillation is initiated through the parallel path formed by loops I and II, as it is illustrated in Fig. 4(b). The single oscillation frequency of 47.9 MHz can be identified from Fig. 5(b). The oscillation frequency of  $f_{osc}^{- \rightarrow 0F}$  can also

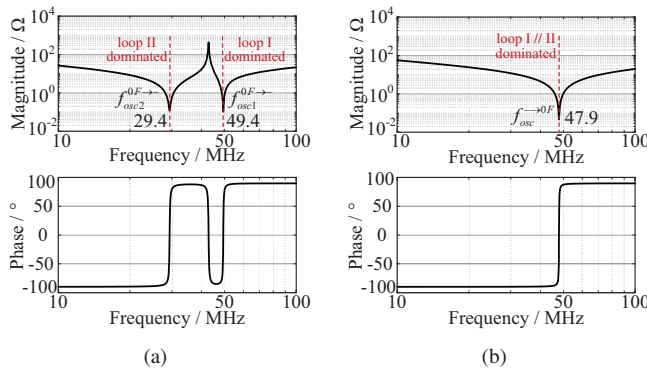


Fig. 5. Circuit impedance analysis of the full-mode equivalent switching circuit. (a) Magnitude and phase during transition “0F → −”. (b) Magnitude and phase during transition “− → 0F”.

be derived by:

$$f_{osc}^{- \rightarrow 0F} = \frac{1}{2\pi \cdot \sqrt{L_{tot}^{- \rightarrow 0F} \cdot C_{oss}}} \quad (2)$$

$$L_{tot}^{- \rightarrow 0F} = \frac{L_{lp1}L_{lp2}}{L_{lp1} + L_{lp2}} + L_{cm} \quad (3)$$

where  $L_{tot}^{- \rightarrow 0F}$  denotes the total loop inductance in equivalence during the transition “− → 0F”, which counts to be 40.9 nH. It is regarded that the components of  $L_{lp1}$  and  $L_{lp2}$  are in parallel during the  $T_4$ 's turn-off oscillation period. Hence, a reduced voltage stress can be expected on switch  $T_4$ .

### B. Outer-Mode Commutation (“− ↔ 0L2” and “+ ↔ 0U2”)

The outer-mode commutation consists of transitions “− ↔ 0L2” and “+ ↔ 0U2” during the negative ( $V_{an} < 0$ ) and positive cycles ( $V_{an} > 0$ ), respectively. The gating signals and circuit diagrams are illustrated in Figs. 6(a) and 6(b), respectively. During the negative cycle, the outer switch  $T_4$  is modulated to be sinusoidal, while the clamping switch  $T_6$  operates complementarily. Simultaneously, the other clamping device  $T_5$  switches identically with  $T_4$  to equalize the voltage stresses between the non-active switches  $T_1$  and  $T_2$ . Turning  $T_5$  off during the “−” state also serves to ensure that the phase current will not commute through the non-neighboring neutral path, i.e., the upper neutral-path enclosing  $T_5$ . Therefore, the load current only commutates between the active phase-arm and its neighboring neutral path, and the main loop I is identified as the major switching loop, which is depicted as the red dashed line in Fig. 6(b). Moreover, the outer mode exhibits two capacitive loops, i.e., the capacitive (capaci.) loop II (or II') and capaci. loop III in Fig. 6(b). Although these capacitive loops do not carry load current, they can also create additional switching-oscillation components.

This can be explained from the equivalent switching circuit of “0L2 → −” (the turn-on transient of  $T_4$ ) as it is demonstrated in Fig. 7(a).  $L_{lp3}$  and  $R_{lp3}$  are the parasitic inductance and resistance of the capacitive loop III. The equivalent switching circuit of “0L2 → −” resembles that of the full-mode commutation “0F → −”. The output capacitors

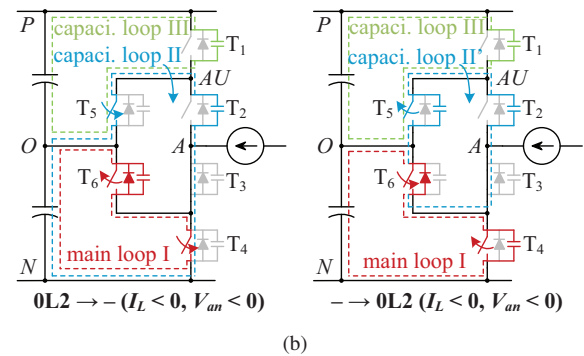
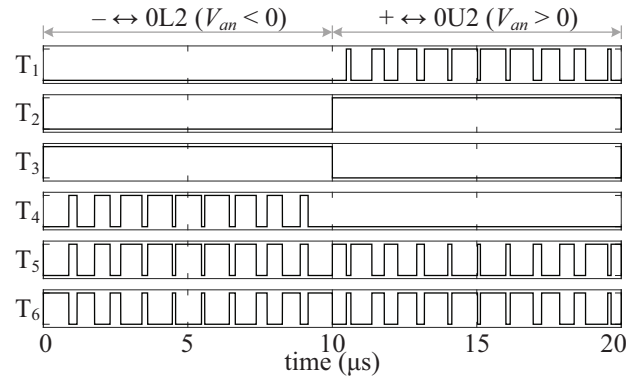


Fig. 6. Outer-mode commutation of the 3L-ANPC phase-leg. (a) Gating signals. (b) Circuit diagrams during transitions “0L2 → −” and “− → 0L2”.

of  $T_6$  and  $T_2$ , i.e.,  $C_{oss,T6}$  and  $C_{oss,T2}$ , are charged through the main loop I and capaci. loop II simultaneously, although  $T_2$  carries no load current during the outer-mode commutation. The output capacitor of  $T_1$  (i.e.,  $C_{oss,T1}$ ) will be charged till  $V_{ds,T1} = V_{bus}/2$  when  $T_5$  is switched on, which creates the capacitive loop III. Nevertheless, the existence of loop III will not affect the switching characteristics of other devices, since loop III is self-closed, and the potential of node AU [see Fig. 7(a)] remains constant as  $V_{bus}/2$  once  $T_5$  is turned on. As it is given in Fig. 8(a), the impedance feature of the switching circuit during “0L2 → −” is identical to that during “0F → −”, and the two oscillation frequencies of  $f_{osc1}^{0L2 \rightarrow -} = 29.4$  MHz and  $f_{osc2}^{0L2 \rightarrow -} = 49.4$  MHz can be obtained by:

$$f_{osc1,osc2}^{0L2 \rightarrow -} = f_{osc1,osc2}^{0F \rightarrow -} = \frac{1}{2\pi} \cdot \sqrt{\frac{L_{lp1} + L_{lp2} + 2L_{cm} \pm \sqrt{(L_{lp1} - L_{lp2})^2 + (2L_{cm})^2}}{2C_{oss} \cdot (L_{lp1}L_{lp2} + L_{lp1}L_{cm} + L_{lp2}L_{cm})}} \quad (4)$$

The equivalent switching circuit of transition “− → 0L2” (the turn-off transient of  $T_4$ ) is demonstrated in Fig. 7(b). As  $C_{oss,T4}$  is charged by the load current and starts to block the dc voltage of  $V_{bus}/2$ , the potential of node AU becomes higher than  $V_{bus}/2$  (equals to  $V_{bus}/2 + V_{ds,T2}$  in respect to BUS−). This is followed by a capacitive discharge of  $C_{oss,T2}$  and  $C_{oss,T1}$  through capacitive loops II' and III respectively, which will be terminated until the steady state “0L2” is reached with:

$$V_{ds,T2}^{0L2} = V_{ds,T5}^{0L2} = V_{bus}/2 - V_{ds,T1}^{0L2}. \quad (5)$$

It is noted that the output capacitance values of  $T_1$ ,  $T_2$ , and  $T_5$  during the state “0L2” can be greater than  $C_{oss} = 270$  pF, as their drain-source voltages (i.e.,  $V_{ds,T1}^{0L2}$ ,  $V_{ds,T2}^{0L2}$ , and  $V_{ds,T5}^{0L2}$ ) are lower than  $V_{bus}/2$ .

A full derivation of the circuit impedance for “ $- \rightarrow 0L2$ ” is given in (6), where the inductance of loop III is also considered. However, letting the imaginary part of  $Z_{detail}^{-\rightarrow 0L2}$  to be zero will engender a high-order equation (greater than second order), which makes the analytical solution unsolvable. Therefore, a simplification is made by omitting  $L_{lp3}$  and  $R_{lp3}$ , so that  $C_{oss,T1}$  can be assumed to be in parallel with  $C_{oss,T5}$ . The circuit impedance after the simplification can be re-written as (7). Then, the dual oscillation frequencies can be derived as (8), where

$$k_c = \frac{C_{oss,T1} + C_{oss,T5}}{C_{oss,T1} + C_{oss,T2} + C_{oss,T5}} \quad (9)$$

$$L_{mix} = \sqrt{L_{lp1}L_{lp2} + L_{lp1}L_{cm} + L_{lp2}L_{cm}} \quad (10)$$

$$C_{oss,T4} = C_{oss}. \quad (11)$$

In (8)-(10), the output capacitances of  $T_1$ ,  $T_2$ , and  $T_5$  are separately modeled, as they can be dependent on the  $C_{oss}$ - $V_{ds}$  characteristics, charging currents, and timing during the “ $- \rightarrow 0L2$ ” transient. This  $C_{oss}$  difference among  $T_1$ ,  $T_2$ , and  $T_5$  can slightly shift the oscillation frequencies to lower levels. Nevertheless, deriving the accurate  $V_{ds}$  and  $C_{oss}$  distributions among  $T_1$ ,  $T_2$ , and  $T_5$  requires further deep and sensitive studies. To simplify, an approximation can be made by assuming  $C_{oss,T1} = C_{oss,T2} = C_{oss,T5} = C_{oss}$ . Thereafter, the impedance comparison between  $Z_{detail}^{-\rightarrow 0L2}$  (full derivation) and  $Z_{simp}^{-\rightarrow 0L2}$  (simplified derivation) are exhibited in Fig. 8(b), where  $Z_{detail}^{-\rightarrow 0L2}$  and  $Z_{simp}^{-\rightarrow 0L2}$  are represented by the dotted and solid curves, respectively. It can be concluded that the simplified derivation is able to characterize the dual oscillation components at 33.6 and 50.9 MHz with satisfactory accuracy, which can also be calculated from (8)-(11). Although the oscillation component at 97.5 MHz is omitted by the simplification (see the impedance curves of  $Z_{detail}^{-\rightarrow 0L2}$  and  $Z_{simp}^{-\rightarrow 0L2}$ ), its resonance energy can be significantly attenuated by the loop resistance at this high-frequency range.

### C. Inner-Mode Commutation (“ $- \leftrightarrow 0U1$ ” and “ $+ \leftrightarrow 0L1$ ”)

The inner mode involves transitions of “ $- \leftrightarrow 0U1$ ” and “ $+ \leftrightarrow 0L1$ ” during the negative and positive cycles, respectively. The gating signals and circuit diagrams of inner-mode commutation are depicted in Figs. 9(a) and 9(b), respectively. The inner mode only operates the switches  $T_2$  and  $T_3$  to be sinusoidal, while other devices conduct per half line-cycle. Then the load current only commutates between the active phase-arm and its non-neighboring neutral path. It can be concluded that only a single switching loop, i.e., the main loop II, is involved during the inner-mode commutation, and no capacitive loop exists as potentials of non-active devices are naturally clamped to dc-bus rails (either P, O, or N).

The equivalent switching circuits for transitions “ $0U1 \rightarrow -$ ” (the turn-on transient of  $T_3$ ) and “ $- \rightarrow 0U1$ ” (the turn-off transient of  $T_3$ ) are depicted in Figs. 10(a) and 10(b), respectively, which are identical except for the junction output capacitor involved (either  $C_{oss,T2}$  or  $C_{oss,T3}$ ). An impedance analysis of the inner-mode switching circuit for both transitions “ $0U1 \rightarrow -$ ” and “ $- \rightarrow 0U1$ ” is depicted in Fig. 11. A single oscillation frequency of  $f_{osc}^{-\leftrightarrow 0U1} = 30.5$  MHz is identified, which can be obtained by:

$$f_{osc}^{-\leftrightarrow 0U1} = \frac{1}{2\pi \cdot \sqrt{L_{tot}^{-\leftrightarrow 0U1} \cdot C_{oss}}} \quad (12)$$

$$L_{tot}^{-\leftrightarrow 0U1} = L_{lp2} + L_{cm} \quad (13)$$

where  $L_{tot}^{-\leftrightarrow 0U1}$  ( $= 100.7$  nH) is the total loop inductance of both inner-mode transitions “ $0U1 \rightarrow -$ ” and “ $- \rightarrow 0U1$ ”.

It is noted the inner mode features a single loop-inductance with a significant value, since its switching loop (i.e., the loop II) contains four switches and it is significantly longer than these of the full mode and outer mode. Moreover, the capacitive charge of inner mode can be notably relieved compared to other commutation modes, as only a single junction output capacitance is involved.

### D. Summary

The switching loops and their associated oscillation frequencies under the three commutation modes are summarized in

$$Z_{detail}^{-\rightarrow 0L2} = \frac{1}{\frac{1}{\frac{1}{j\omega C_{oss,T1}} + j\omega L_{lp3} + R_{lp3}} + \frac{1}{j\omega C_{oss,T5}} + \frac{1}{j\omega C_{oss,T2}} + j\omega L_{lp2} + R_{lp2} + R_{on}} + \frac{1}{R_{lp1} + R_{on} + j\omega L_{lp1}}} + R_{cm} + j\omega L_{cm} + \frac{1}{j\omega C_{oss,T4}} \quad (6)$$

$$Z_{simp}^{-\rightarrow 0L2} = \frac{1}{\frac{1}{j\omega(C_{oss,T1} + C_{oss,T5})} + \frac{1}{j\omega C_{oss,T2}} + j\omega L_{lp2} + R_{lp2} + R_{on}} + \frac{1}{R_{lp1} + R_{on} + j\omega L_{lp1}}} + R_{cm} + j\omega L_{cm} + \frac{1}{j\omega C_{oss,T4}} \quad (7)$$

$$f_{osc1,osc2}^{-\rightarrow 0L2} = \frac{1}{2\pi} \cdot \sqrt{\frac{\frac{L_{lp1} + L_{cm}}{C_{oss,T2}} + \frac{k_c(L_{lp1} + L_{lp2})}{C_{oss,T4}} \pm \sqrt{\left(\frac{L_{lp1} + L_{cm}}{C_{oss,T2}}\right)^2 + \left(\frac{k_c(L_{lp1} + L_{lp2})}{C_{oss,T4}}\right)^2} + \frac{2k_c(L_{lp1}^2 - L_{mix}^2)}{C_{oss,T2} \cdot C_{oss,T4}}}{2k_c \cdot L_{mix}^2}} \quad (8)$$

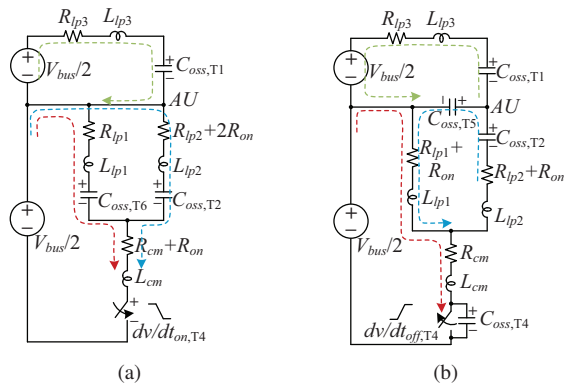


Fig. 7. Equivalent switching circuits of the outer-mode commutation. (a) Equivalent switching circuit during transition “0L2 → -”. (b) Equivalent switching circuit during transition “- → 0L2”.

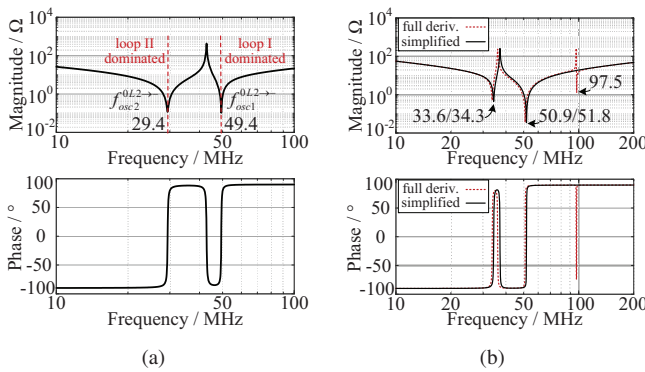


Fig. 8. Circuit impedance analysis of the outer-mode equivalent switching circuit. (a) Magnitude and phase during transition “0L2 → -”. (b) Magnitude and phase during transition “- → 0L2”.

Table IV. It can be observed that the full-mode and outer-mode commutations feature homogeneous characteristics during the turn-on transient of  $T_4$  (i.e., transitions of “0F → -” and “0L2 → -”), as dual oscillation frequencies of 29.4 MHz and 49.4 MHz can be derived. The “- → 0F” transient of the full-mode commutation (i.e., the turn-off transient of  $T_4$ ) exhibits a single switching-oscillation at 47.9 MHz as loops I and II are regarded to be combined in parallel. Nevertheless, the transition “- → 0L2” of the outer-mode commutation is more complicated as it involves main loop I and capacitive loops II’ and III. Three oscillation frequencies of 34.3 MHz, 51.8 MHz, and 97.5 MHz can be obtained based on the full derivation from (6). On the other hand, the inner mode features the most straightforward switching characteristic, as a single switching loop is concerned for both transients “0U1 → -” and “- → 0U1”. A single oscillation component at 30.5 MHz is calculated accordingly.

#### IV. EXPERIMENTAL ASSESSMENTS OF SWITCHING CHARACTERISTICS FOR SiC MOSFETs IN 3L-ANPC INVERTERS

In order to evaluate the switching oscillations and other switching characteristics of the SiC MOSFETs in the 3L-ANPC inverter, the standard DPTs are performed under the

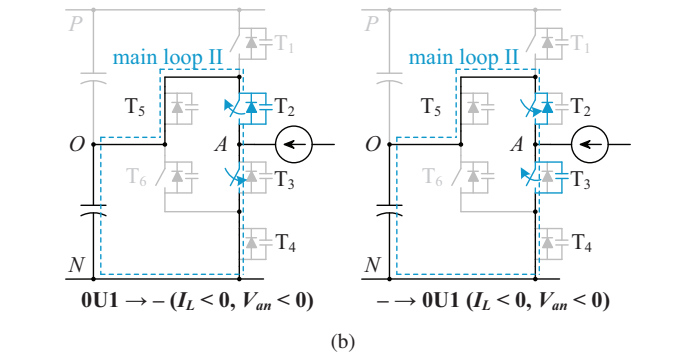
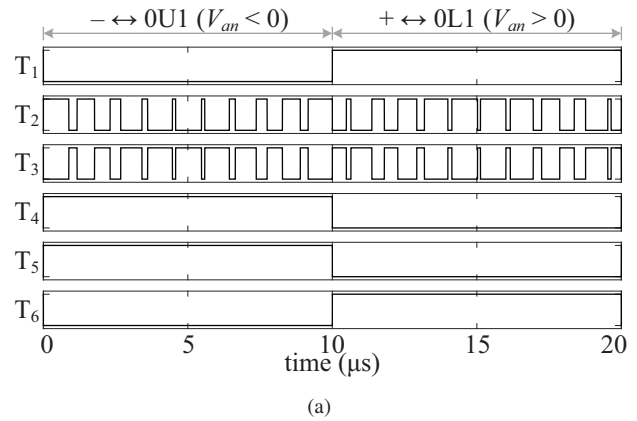


Fig. 9. Inner-mode commutation of the 3L-ANPC phase-leg. (a) Gating signals. (b) Circuit diagrams during transitions “0U1 → -” and “- → 0U1”.

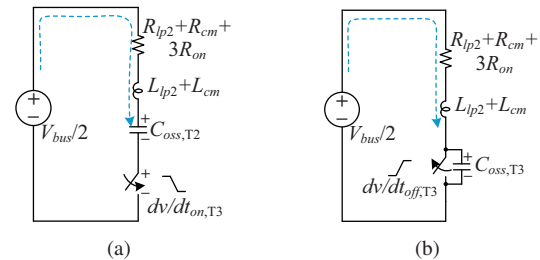


Fig. 10. Equivalent switching circuits of the inner-mode commutation. (a) Equivalent switching circuit during transition “0U1 → -”. (b) Equivalent switching circuit during transition “- → 0U1”.

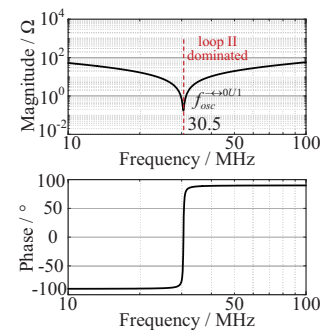


Fig. 11. Circuit impedance analysis of the inner-mode equivalent switching circuit during transitions of “0U1 → -” and “- → 0U1”.

full-mode, outer-mode, and inner-mode commutations. In this section, the DPT setup is illustrated first, and the switching



TABLE IV  
SUMMARY OF SWITCHING LOOPS AND OSCILLATION FREQUENCIES UNDER THE THREE 3L-ANPC COMMUTATION MODES.

| Modes | Loops involved             | Symbols  | Oscillation frequencies                 |
|-------|----------------------------|--|---|
| Full  | Main I, II                 | $f_{osc1}^{0F \rightarrow -}$ , $f_{osc2}^{0F \rightarrow -}$<br>$f_{osc}^{- \rightarrow 0F}$                                      | 29.4, 49.4 MHz<br>47.9 MHz              |
| Outer | Main I and capaci. II, III | $f_{osc1}^{0L2 \rightarrow -}$ , $f_{osc2}^{0L2 \rightarrow -}$<br>$f_{osc1}^{- \rightarrow 0L2}$ , $f_{osc2}^{- \rightarrow 0L2}$ | 29.4, 49.4 MHz<br>34.3, 51.8 , 97.5 MHz |
| Inner | Main II                    | $f_{osc}^{- \leftrightarrow 0U1}$  | 30.5 MHz                                |

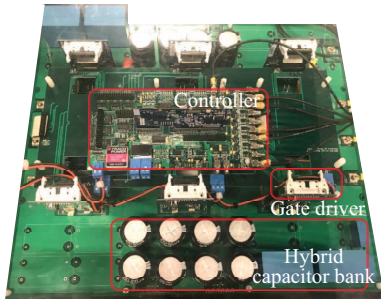


Fig. 12. Top view of a 1500-V SiC-based 3L-ANPC inverter demonstrator.

TABLE V  
EQUIPMENT USED FOR DOUBLE PULSE TEST (DPT).

| Category           | Manufacturer      | Model             |
|--------------------|-------------------|-------------------|
| DC source          | Elektro-Automatik | PSI-800-3U-HS-PV  |
| Load inductor      | —                 | 190 $\mu$ H       |
| Controller         | Texas Instrument  | TMS320F28379D     |
| Gate driver        | CREE/Wolfspeed    | CGD15HB62P1       |
| SiC module         | Microsemi         | APTMC120AM55CT1AG |
| Passive probe      | Lecroy            | PP019 and PPE 2kV |
| Differential probe | Tektronix         | P5200A            |
| Current transducer | PEM               | CWTUM/6/R         |

waveforms of the three commutation modes are then exhibited.

### A. DPT Setup

A 3L-ANPC inverter demonstrator is implemented as shown in Fig. 12 by adopting the structural design illustrated in Section II, which is tested as the DPT setup. A hybrid capacitor bank utilizing both Al-Caps and MPPF-Caps is also implemented. A four-layer laminated PCB integrates both the dc bus and the aforementioned ANPC phase-leg. The equipment used for DPT are listed in Table V. A 1500-V dc-source PSI-800-3U-HS-PV is applied to energize the dc bus (from BUS+ to BUS-). CREE’s SiC MOSFET driver CGD15HB62P1 is used, and the fixed gate voltages of +20 V and -5 V are utilized. A 190  $\mu$ H load inductor is implemented using 1.6 mm Litz wire and dual sendust powder cores.

The fundamental principles of the DPT can be seen in details in [44]. The BUS- rail and the oscilloscope are grounded, and only negative-cycle commutations “-  $\leftrightarrow$  0F”, “-  $\leftrightarrow$  0L2”, and “-  $\leftrightarrow$  0U1” are tested as the representatives of the full-

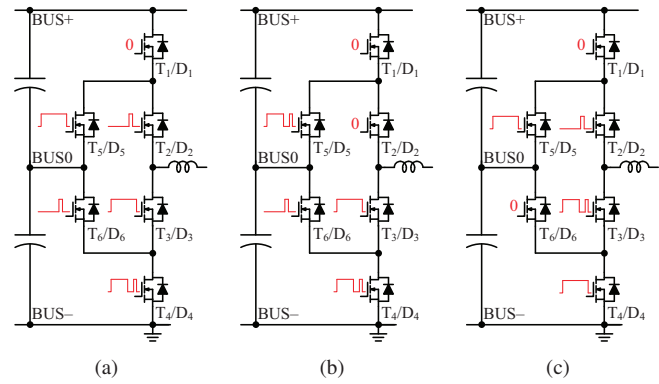


Fig. 13. Double-pulse configurations for the 3L-ANPC phase-leg under the three commutation modes. (a) The full mode “-  $\leftrightarrow$  0F”. (b) The outer mode “-  $\leftrightarrow$  0L”. (c) The inner mode “-  $\leftrightarrow$  0U1”.

mode, outer-mode, the inner-mode commutations, respectively. Three different DPT configurations are implemented to simulate the switching behaviors of the three commutation modes under sinusoidal load currents, which are demonstrated in Figs. 13(a), 13(b), and 13(c), respectively. The gate-source and drain-source voltages of  $T_4$  (i.e.,  $V_{gs,T4}$  and  $V_{ds,T4}$ ) are measured using Lecroy’s passive probes PP019 and PPE-2kV, respectively. Other voltage waveforms of  $V_{gs,T3}$ ,  $V_{ds,T2}$ ,  $V_{ds,T3}$  and  $V_{ds,T6}$  are captured by differential probes P5200A as they have floating potentials to the earth. The drain currents of switches  $T_3$  and  $T_4$  (i.e.,  $I_{d,T3}$  and  $I_{d,T4}$ ) are measured using PEM’s current transducers CWTUM/6/R.

### B. Transient Switching Waveforms

Multiple DPTs are performed under the rated condition of  $V_{bus} = 1000$  V and  $I_L = -40$  A. An external capacitance  $C_{gs,ext} = 3.3$  nF is applied to the gate-source terminal of each SiC MOSFET to mitigate the cross-talking issue [45], [46]. Multiple external gate resistances (i.e.,  $R_{g,ext} = 5.5$   $\Omega$ , 11  $\Omega$ , 16  $\Omega$ , and 25  $\Omega$ ) are tested to evaluate the switching performances under switching-speed variations.

The transient switching waveforms of the gate-source voltage  $V_{gs}$ , the drain current  $I_d$ , and the drain-source voltage  $V_{ds}$ , of the active switch under the three commutation modes (i.e.,  $T_4$  for the full mode and outer mode, and  $T_3$  for the inner mode) are captured and presented in Figs. 14, 15, and 16. The voltage and current waveforms captured under  $R_{g,ext} = 5.5$   $\Omega$ , 11  $\Omega$ , 16  $\Omega$ , and 25  $\Omega$  are depicted as curves in black, blue, red, and green, respectively. The slew rates of drain-source voltages (i.e., the  $dv/dt$ ) are in the range from 37.0 V/ns to 10.9 V/ns, as the  $R_{g,ext}$  varies from 5.5  $\Omega$  to 25  $\Omega$ . Concurrently, the slew rates of drain currents (i.e., the  $di/dt$ ) are in the range from 4.3 A/ns to 1.0 A/ns.

In general, the voltage and current slew rates decrease with the increase of the external gate resistance, while the switching delay increases. Due to the high switching-speed of the SiC MOSFET, drain-current overshoots and oscillations are observed during the turn-on transients. Similarly, voltage overshoots with significant switching oscillations are exhibited during the turn-off transients. The detailed analysis and com-

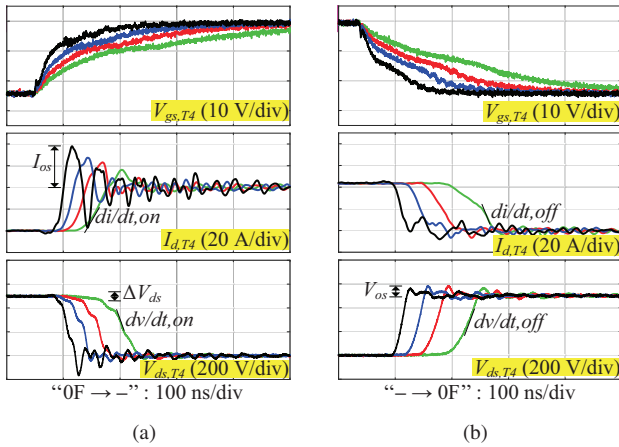


Fig. 14. Full-mode commutation waveforms under the conditions of  $V_{bus} = 1000$  V,  $I_L = -40$  A,  $R_{g,ext} = 5.5$   $\Omega$ , 11  $\Omega$ , 16  $\Omega$ , and 25  $\Omega$ , and  $C_{gs,ext} = 3.3$  nF. (a) Turn-on waveforms of  $V_{gs,T4}$ ,  $I_{d,T4}$ , and  $V_{ds,T4}$ . (b) Turn-off waveforms of  $V_{gs,T4}$ ,  $I_{d,T4}$ , and  $V_{ds,T4}$ .

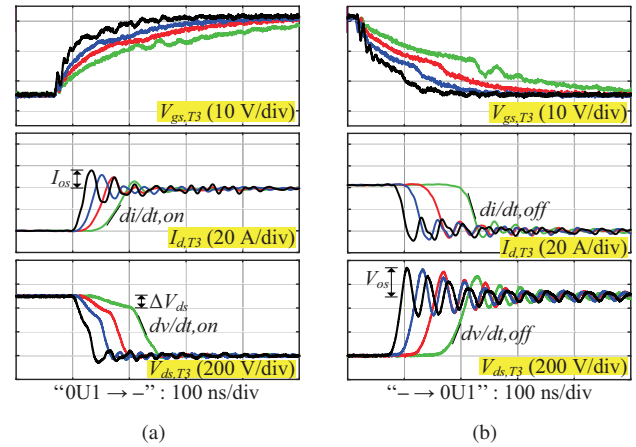


Fig. 16. Inner-mode commutation waveforms under the conditions of  $V_{bus} = 1000$  V,  $I_L = -40$  A,  $R_{g,ext} = 5.5$   $\Omega$ , 11  $\Omega$ , 16  $\Omega$ , and 25  $\Omega$ , and  $C_{gs,ext} = 3.3$  nF. (a) Turn-on waveforms of  $V_{gs,T3}$ ,  $I_{d,T3}$ , and  $V_{ds,T3}$ . (b) Turn-off waveforms of  $V_{gs,T3}$ ,  $I_{d,T3}$ , and  $V_{ds,T3}$ .

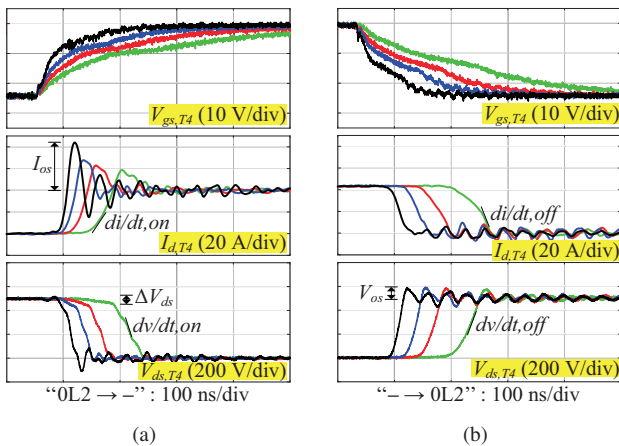


Fig. 15. Outer-mode commutation waveforms under the conditions of  $V_{bus} = 1000$  V,  $I_L = -40$  A,  $R_{g,ext} = 5.5$   $\Omega$ , 11  $\Omega$ , 16  $\Omega$ , and 25  $\Omega$ , and  $C_{gs,ext} = 3.3$  nF. (a) Turn-on waveforms of  $V_{gs,T4}$ ,  $I_{d,T4}$ , and  $V_{ds,T4}$ . (b) Turn-off waveforms of  $V_{gs,T4}$ ,  $I_{d,T4}$ , and  $V_{ds,T4}$ .

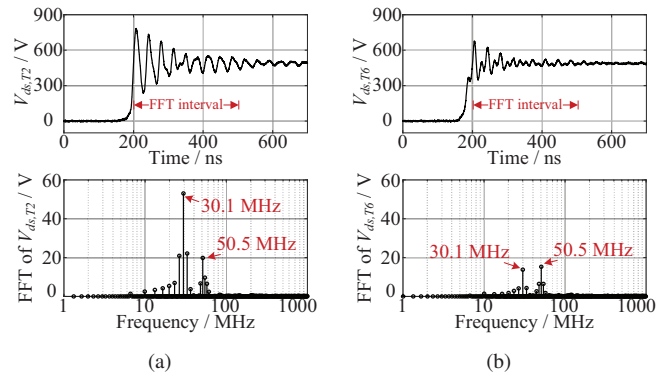


Fig. 17. Time-domain waveforms and frequency spectrums for the full-mode commutation “0F  $\rightarrow$  -” under the DPT condition of  $V_{bus} = 1000$  V,  $I_L = -40$  A,  $R_{g,ext} = 5.5$   $\Omega$ , and  $C_{g,ext} = 3.3$  nF. (a)  $V_{ds,T2}$  during “0F  $\rightarrow$  -”. (b)  $V_{ds,T6}$  during “0F  $\rightarrow$  -”.

parison of switching oscillations and other characteristics will be discussed in the following sections.

## V. ANALYSIS OF EXPERIMENTAL RESULTS I: SWITCHING OSCILLATIONS

In this section, fast Fourier transform (FFT) analyses are conducted on the switching waveforms of drain-source voltages (i.e.,  $V_{ds,Tx}$ ,  $x = 2, 3, 4$ , and 6) under the DPT condition of  $V_{bus} = 1000$  V,  $I_L = -40$  A,  $R_{g,ext} = 5.5$   $\Omega$ , and  $C_{gs,ext} = 3.3$  nF. Subsequently, the equivalent switching circuits and switching oscillations studied in Section III are validated. The FFT results of  $V_{ds,Tx}$  for the three commutation modes will be discussed respectively in the following sub-sections.

It should be pointed out that the drain-current measurements are not utilized to characterize the switching oscillations in this section, as the current transducer features a limited bandwidth of 30 MHz. Although the differential voltage probe P5200A features a bandwidth of 50 MHz, its frequency identifications

near 50 MHz are still valid, as the probe will not introduce a frequency shift to the measurements.

### A. FFT Results of Full-Mode Commutation

For the “0F  $\rightarrow$  -” transient of full-mode commutation, the switching waveforms of  $V_{ds,T2}$  and  $V_{ds,T6}$  are utilized for the FFT analysis. The frequency spectrums of  $V_{ds,T2}$  and  $V_{ds,T6}$  as well as time-domain waveforms are depicted in Figs. 17(a) and 17(b) respectively (as black solid lines). A 300-ns time interval is sampled for the FFT analysis, which starts from the instant that  $V_{ds,T2}$  (or  $V_{ds,T6}$ ) first crosses  $V_{bus}/2$ . A Hamming window function is used to prevent spectral leakages. To validate these voltage measurements by the differential probe P5200A, LTspice simulation results of  $V_{ds,T2}$  and  $V_{ds,T6}$  in both time- and frequency-domain are also exhibited in Fig. 17 (as red dashed lines). Simulation waveforms of both  $V_{ds,T2}$  and  $V_{ds,T6}$  can match with their experimental results, and identical oscillation components can be found from their frequency spectrums.

The measured oscillation frequencies and the errors versus their theoretical expectations are summarized in Table VI. It

TABLE VI  
FFT RESULTS OF MEASURED DRAIN-SOURCE VOLTAGES UNDER THREE 3L-ANPC COMMUTATION TYPES.

| Commutation types |           | $V_{ds}$ studied | Oscillation frequencies | Theoretical errors |
|-------------------|-----------|------------------|-------------------------|--------------------|
| Full              | “0F → -”  | $V_{ds,T2}$      | 30.1 & 50.5 MHz         | 0.7 & 1.1 MHz      |
|                   |           | $V_{ds,T6}$      | 30.1 & 50.5 MHz         | 0.7 & 1.1 MHz      |
|                   | “- → 0F”  | $V_{ds,T4}$      | 44.3 MHz                | 3.6 MHz            |
| Outer             | “OL2 → -” | $V_{ds,T6}$      | 29.9 & 49.9 MHz         | 0.5 MHz            |
|                   | “- → OL2” | $V_{ds,T4}$      | 32.8 & 52.4 MHz         | 1.5 & 0.6 MHz      |
| Inner             | “0U1 → -” | $V_{ds,T2}$      | 29.7 MHz                | 2.6 MHz            |
|                   | “- → 0U1” | $V_{ds,T3}$      | 28.3 MHz                | 2.2 MHz            |

is observed that a single switch may have multiple oscillation components, although it is enclosed in a single loop. This phenomenon can be explained by the mutual-interference effect between loops. Specifically, dual oscillation frequencies of 30.1 and 50.5 MHz can be obtained from both  $V_{ds,T2}$  and  $V_{ds,T6}$ . The theoretical expectations discussed in Section III (i.e., 29.4 and 49.4 MHz) deviate with these obtained by experiment by 0.7 and 1.1 MHz, respectively, which are induced by estimation errors on loop inductance and device output capacitance. Regarding oscillation magnitudes on  $V_{ds,T2}$ , the low-frequency oscillation (i.e., 30.1 MHz) is more significant than its high-frequency counterpart (i.e., 50.5 MHz). Since switch  $T_2$  is enclosed by loop II, which features higher inductive energy ( $L_{lp2} = 78.2$  nH) and dominates the low-frequency oscillation at 30.1 MHz. On the other hand, the magnitudes of high-frequency oscillations on  $V_{ds,T6}$  are significantly reduced, as loop I (which encloses  $T_6$ ) has less inductive energy ( $L_{lp1} = 24.1$  nH). The low-frequency component exhibits comparable oscillation amplitude on  $V_{ds,T6}$ .

The frequency spectrum of  $V_{ds,T4}$  and its time-domain waveform during the “- → 0F” transient are exhibited in Fig. 18. It can be observed that the oscillation amplitudes of  $V_{ds,T4}$  (i.e., the voltage overshoot) may be neglected compared to these of  $V_{ds,T2}$  and  $V_{ds,T6}$  (during  $T_4$ ’s turn-on transient). As it is discussed in Section III-A, the inductance components of  $L_{lp1}$  and  $L_{lp2}$  can be regarded to be in parallel connection during  $T_4$ ’s turn-off transient. Due to this paralleling effect, The equivalent loop inductance during  $T_4$ ’s turn-off transient is significantly reduced, and lower oscillation amplitude shall be expected. On the other aspect, the drain-current  $di/dt$  during  $T_4$ ’s turn-on transient is greater than that during its turn-off transient, as one identical gate resistance  $R_{g,ext} = 5.5 \Omega$  is adopted for both the turn-on and turn-off intervals.

Three oscillation components are identified in Fig. 18 with oscillation frequencies of 34.9, 44.3, and 60.1 MHz. The theoretical derivation successfully predicts the middle oscillation frequency of 44.3 MHz with an error of 3.6 MHz (as noted in Table VI), while the oscillation components at 34.9 MHz and 60.1 MHz are omitted as they are engendered by the asymmetrical turn-on of SBDs of  $T_2$  and  $T_6$ , which can not be characterized by the theoretical derivation. To elaborate this issue, Fig. 19 exhibits the simulated diode-forward-current  $I_f$  and drain-source-voltage  $V_{ds}$  waveforms of  $T_2$  and  $T_6$  during

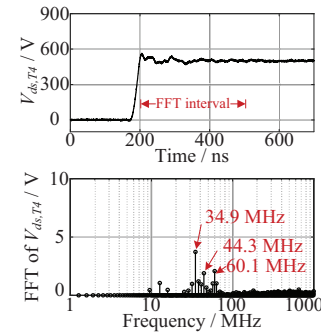


Fig. 18. Time-domain waveform and frequency spectrum of  $V_{ds,T4}$  for the full-mode commutation “- → 0F” under the DPT condition of  $V_{bus} = 1000$  V,  $I_L = -40$  A,  $R_{g,ext} = 5.5 \Omega$ , and  $C_{g,ext} = 3.3$  nF.

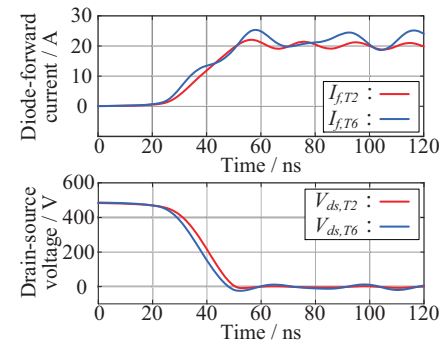


Fig. 19. The diode-forward currents  $I_f$  and drain-source voltages  $V_{ds}$  of  $T_2$  and  $T_6$  during the full-mode transition “- → 0F”.

the full-mode transition “- → 0F”. Due to the more significant inductance of loop II (i.e.,  $L_{lp2} > L_{lp1}$ ), the turn-on operation of  $T_2$ ’s SBD is delayed compared with that of  $T_6$ ’s SBD during the interval of 20–60 ns. Furthermore,  $I_{f,T6}$  exhibits a higher  $di/dt$  than  $I_{f,T2}$  during the simulation interval of 20–40 ns, and it starts to oscillate before the complete conduction of  $T_2$ ’s SBD. In such circumstance, other unexpected oscillation components can be activated.

### B. FFT Results of Outer-Mode Commutation

The spectrum of  $V_{ds,T6}$  during the transient “OL2 → -” is depicted in Fig. 20(a). As the equivalent switching circuit of outer-commutation “OL2 → -” resembles that of the full-commutation “0F → -”, the frequency spectrum of  $V_{ds,T6}$  during “OL2 → -” exhibits analogous oscillation frequencies (i.e., 29.9 and 49.9 MHz) and magnitudes as these of  $V_{ds,T6}$  during “0F → -”. A frequency error of 0.5 MHz is observed between the experimental analyses and theoretical expectations.

Regarding the “- → OL2” transient, the frequency spectrum of  $V_{ds,T4}$  is different from that during the “- → 0F” transient, as it is depicted in Fig. 20(b). Dual oscillation frequencies of 32.8 and 52.4 MHz can be identified accordingly. Besides, the voltage oscillation magnitudes become more significant than these during “- → 0F”, especially the low-frequency one at 32.8 MHz. The oscillation component at 97.5 MHz is missing from the frequency spectrum of  $V_{ds,T4}$ , as its resonance energy is limited and can be significantly attenuated by the loop resistance at this high-frequency range.

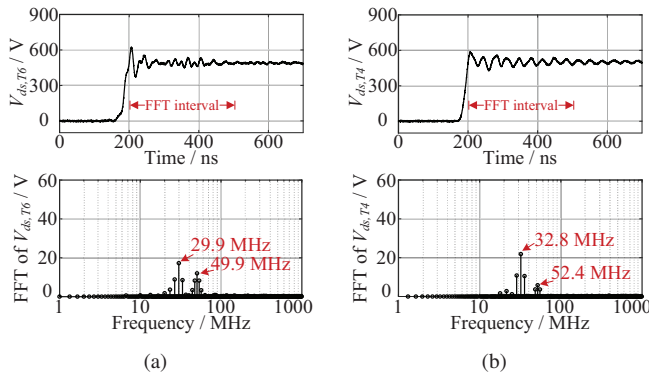


Fig. 20. Time-domain waveforms and frequency spectrums for the outer-mode commutations “0L2 → -” and “- → 0L2” under the DPT condition of  $V_{bus} = 1000$  V,  $I_L = -40$  A,  $R_{g,ext} = 5.5$   $\Omega$ , and  $C_{g,ext} = 3.3$  nF. (a)  $V_{ds,T6}$  during “0L2 → -”. (b)  $V_{ds,T4}$  during “- → 0L2”.

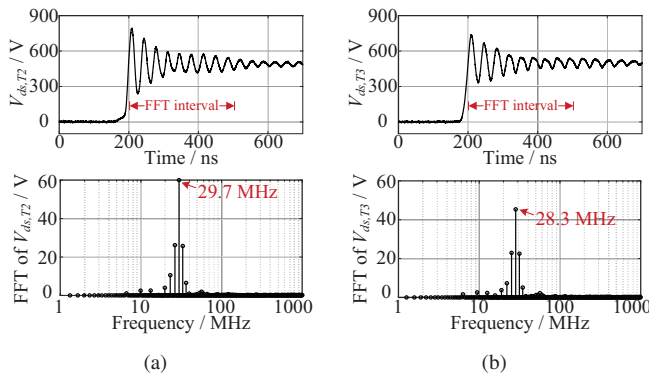


Fig. 21. Time-domain waveforms and frequency spectrums for the inner-mode commutations “0U1 → -” and “- → 0U1” under the DPT condition of  $V_{bus} = 1000$  V,  $I_L = -40$  A,  $R_{g,ext} = 5.5$   $\Omega$ , and  $C_{g,ext} = 3.3$  nF. (a)  $V_{ds,T2}$  during “0U1 → -”. (b)  $V_{ds,T3}$  during “- → 0U1”.

### C. FFT Results of Inner-Mode Commutation

The frequency spectrums and time-domain waveforms of  $V_{ds,T2}$  during “0U1 → -” and  $V_{ds,T3}$  during “- → 0U1” are exhibited in Figs. 21(a) and 21(b) respectively. As it is illustrated in Section III, a single oscillation frequency can be found from each commutation transient. Specifically, the oscillation components at 29.7 and 28.3 MHz can be identified from Figs. 21(a) and 21(b) respectively (with frequency errors of 2.6 and 2.2 MHz compared to theoretical expectations). Additionally, the oscillation amplitudes of both  $V_{ds,T2}$  and  $V_{ds,T3}$  during the inner commutations are comparable with that of  $V_{ds,T2}$  during the full commutation. A comparison of the oscillation peaks (i.e., voltage overshoots) of  $V_{ds,Tx}$  ( $x = 2, 3, 4,$  and  $6$ ) under the three commutation types will be studied in the following section.

## VI. ANALYSIS OF EXPERIMENTAL RESULTS II: OTHER SWITCHING CHARACTERISTICS AND DESIGN CONSIDERATIONS

With the differences in terms of switching loops, the three commutation modes also feature differences on other switching characteristics such as voltage overshoot, current

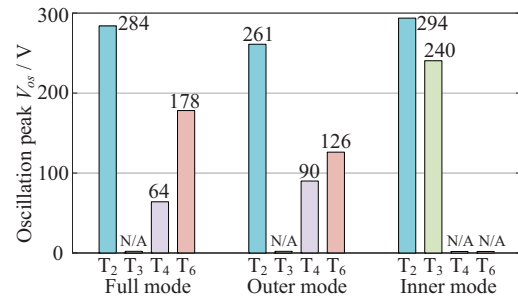


Fig. 22. Comparison of voltage overshoots  $V_{os}$  (oscillation peaks) on  $T_2$ ,  $T_3$ ,  $T_4$ , and  $T_6$  under the DPT condition of  $V_{bus} = 1000$  V,  $I_L = -40$  A,  $R_{g,ext} = 5.5$   $\Omega$ , and  $C_{g,ext} = 3.3$  nF.

overshoot, capacitive charge, and switching energy. These switching characteristics are exhibited and benchmarked in this section. Then, design guidelines specified for different commutation modes are proposed.

### A. Drain-Source Voltage Overshoots (Oscillation Peaks)

A comparison of voltage overshoots  $V_{os}$  (i.e., oscillation peaks) exposed on switching devices  $T_2$ ,  $T_3$ ,  $T_4$ , and  $T_6$  under the DPT condition of  $V_{bus} = 1000$  V,  $I_L = -40$  A,  $R_{g,ext} = 5.5$   $\Omega$ , and  $C_{gs,ext} = 3.3$  nF is indicated in Fig. 22. It is noted that inner switches  $T_2$  and  $T_3$  ( $T_3$  is only applicable for the inner-mode commutation) suffer the greatest voltage overshoots of  $V_{os} = 240$ – $294$  V, since they are enclosed by the loop II with high loop-inductance ( $L_{lp2} + L_{cm} = 100.7$  nH), which leads to elevated voltage overshoots according to:

$$V_{os} = L_{loop} \cdot di/dt_{off} \quad (14)$$

where  $L_{loop}$  and  $di/dt_{off}$  denote the overall loop inductance and turn-off slew rate of device current, respectively. It has also been obtained that these high-voltage overshoots on inner devices are dominated by oscillation components with the low-frequency range from 28.3 to 30.1 MHz.

In contrast, the clamping device  $T_6$  exhibits lower voltage stresses for both full and outer modes ( $V_{os} = 126$ – $178$  V), as it is involved in the loop I with  $L_{lp1} + L_{cm} = 46.6$  nH. Moreover, the active switch  $T_4$  features the lowest voltage-overshoot of  $V_{os} = 64$ – $90$  V for the full and outer commutations.

### B. Drain-Current Overshoots and Total Capacitive Charges

During turn-on transients, the SiC MOSFET is characterized by a significant drain current overshoot, which is caused by the capacitive charges contributed by  $C_{oss}$  of the complementary devices. As it is exhibited in Fig. 23(a), the drain current overshoots  $I_{os}$  exhibit dependencies on both the commutation type and external gate resistance. The inner mode features the minimum  $I_{os}$ , while the outer mode and full mode reveal  $I_{os}$  amplitudes higher than 40 A under the condition of  $R_{g,ext} = 5.5$   $\Omega$ . This variation is caused by differences in the total capacitive charge during the turn-on transient. For the full-mode and outer-mode commutations,  $C_{oss,T2}$  and  $C_{oss,T6}$  shall be charged to  $\frac{1}{2} \cdot V_{bus}$  during the turn-on transient of switch  $T_4$  (i.e., “0F → -” and “0L2 → -”, respectively).

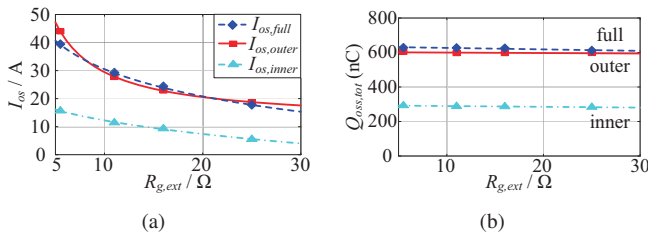


Fig. 23. Measured turn-on drain current overshoots and total capacitive charges of the full-mode, outer-mode, and inner-mode commutations under the DPT condition of  $V_{bus} = 1000$  V and  $I_L = -40$  A. (a) Turn-on drain current overshoots  $I_{os}$ . (b) Total capacitive charges  $Q_{oss,tot}$ .

Considering the non-linearity of  $C_{oss}$ , the total capacitive charge  $Q_{oss,tot}$  of the full-mode and outer-mode commutations are calculated as 599.8 nC according to:

$$Q_{oss,tot}^{0F \rightarrow -}, Q_{oss,tot}^{0L2 \rightarrow -} = \int_0^{\frac{1}{2}V_{bus}} (C_{oss,T2} + C_{oss,T6}) dv \quad (15)$$

Furthermore, as only  $C_{oss,T2}$  is charged during the inner-mode commutation “0U1  $\rightarrow$  -”, the capacitive charge of inner mode is derived as 299.9 nC by:

$$Q_{oss,tot}^{0U1 \rightarrow -} = \int_0^{\frac{1}{2}V_{bus}} C_{oss,T2} dv \quad (16)$$

The total capacitive charge  $Q_{oss,tot}$  can also be measured by integrating the transient drain-current overshoots during the turn-on interval of the active switch. Fig. 23(b) exhibits those measured  $Q_{oss,tot}$  with respect to the external gate resistance  $R_{g,ext}$  under the DPT condition of  $V_{bus} = 1000$  V and  $I_L = -40$  A. It can be obtained that the measured  $Q_{oss,tot}$  can be regarded as being independent of  $R_{g,ext}$ . Additionally, the full mode and outer mode exhibit twice the  $Q_{oss,tot}$  featured by the inner-mode commutation, both of which match with the theoretical derivations from (12) and (13).

### C. Switching Energies

The turn-on and turn-off switching energies  $E_{on}$  and  $E_{off}$  of the active switch under the DPT condition of  $V_{bus} = 1000$  V and  $R_{g,ext} = 11 \Omega$  are exhibited in Figs. 24(a) and 24(b), respectively, which are calculated by integrating the term  $I_{d,Tx} \times V_{ds,Tx}$  during switching transients. It is noted that the current probe CWTUM/6/R features a peak  $di/dt$  of 70 A/ns, which is capable of capturing the rising/falling slope of the drain current. Moreover, a deskew process is performed to align the drain-current and drain-source-voltage waveforms. It can be observed that the full mode and outer mode exhibit excessive turn-on energies (e.g.,  $E_{on,full} = 550 \mu\text{J}$  and  $E_{on,outer} = 560 \mu\text{J}$  under  $I_d = 40$  A) compared to that of the inner mode ( $E_{on,inner} = 390 \mu\text{J}$ ), as parts of energies stored in  $C_{oss,T2}$  and  $C_{oss,T6}$  shall be counted in both  $E_{on,full}$  and  $E_{on,outer}$ . On the other hand, their turn-off energies  $E_{off,full}$  and  $E_{off,outer}$  are relieved compared to  $E_{off,inner}$ , since the energies stored in  $C_{oss,T2}$  and  $C_{oss,T6}$  are released during the turn-off transient of  $T_4$  and cause a reduction on  $E_{off,full}$  and  $E_{off,outer}$ .

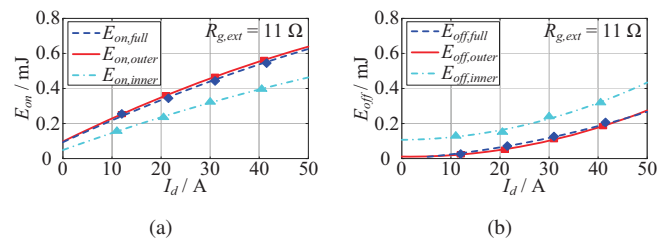


Fig. 24. Measured turn-on and turn-off switching energies of the full-mode, the outer-mode, and the inner-mode commutations under  $V_{bus} = 1000$  V,  $R_{g,ext} = 11 \Omega$ , and  $C_{g,ext} = 3.3$  nF. (a) Turn-on switching energies  $E_{on}$ . (b) Turn-off switching energies  $E_{off}$ .

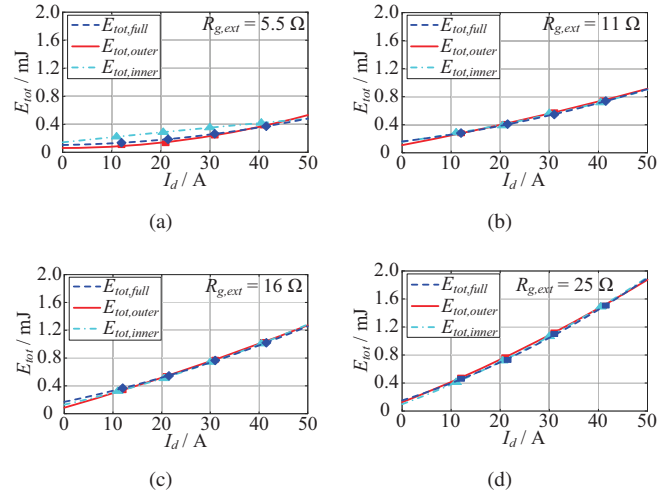


Fig. 25. Measured total switching energies  $E_{tot}$  of the outer-mode, the inner-mode, and the full-mode commutations. (a)  $R_{g,ext} = 5.5 \Omega$ . (b)  $R_{g,ext} = 11 \Omega$ . (c)  $R_{g,ext} = 16 \Omega$ . (d)  $R_{g,ext} = 25 \Omega$ .

Additionally, the total switching energies per cycle ( $E_{tot} = E_{on} + E_{off}$ ) under  $R_{g,ext} = 5.5 \Omega$ ,  $11 \Omega$ ,  $16 \Omega$ , and  $25 \Omega$  are shown in Figs. 25(a), 25(b), 25(c), and 25(d), respectively. Overall, the total switching energies  $E_{tot}$  of the three commutation modes are comparable under  $R_{g,ext} = 11 \Omega$ ,  $16 \Omega$ , and  $25 \Omega$ . Nevertheless, under the condition of  $R_{g,ext} = 5.5 \Omega$ , the  $E_{tot}$  of inner mode exceeds these of the full mode and outer mode by 40–100  $\mu\text{J}$  throughout the drain-current range of 10–40 A. This can be explained since the switching speed of inner mode can be limited by its more significant loop inductance (contributed by main loop II), especially under a low gate resistance condition (e.g.,  $R_{g,ext} = 5.5 \Omega$ ).

### D. Summaries and Design Considerations

As a summary, switching characteristics of the three commutation modes obtained from DPTs are listed in Table VII, which reveals details in terms of switching oscillations, current overshoots, switching energies, and capacitive charges. It can be concluded that the full mode and outer mode have several similarities, as both of them feature multiple switching loops and oscillation components, as well as excessive current overshoots, switching energies, and capacitive charges. Nevertheless, all of the three types of commutation will induce critical lower-frequency (28.3–30.1 MHz) oscillation peaks on

TABLE VII  
SUMMARY OF SWITCHING CHARACTERISTICS OF SiC MOSFETS IN THE 3L-ANPC DEMONSTRATOR.

| Commutation types |           | Oscillation frequencies<br>In Table IV | Critical Oscillations<br>In Fig. 22 | Current overshoots<br>In Fig. 23(a) | Switching energies<br>In Fig. 24 | Capacitive charges<br>In Fig. 23(b)          |
|-------------------|-----------|--|-------------------------------------|-------------------------------------|----------------------------------|--|
| Full              | “0F → -”  | 30.1 & 50.5 MHz                        | T <sub>2</sub> @ 284V, 30.1MHz      | 39 A                                | 550 μJ                           | 599.8 nC                                     |
|                   | “- → 0F”  | 44.3 MHz                               | —                                   | —                                   | 200 μJ                           | (Q <sub>oss,T2</sub> + Q <sub>oss,T6</sub> ) |
| Outer             | “0L2 → -” | 29.9 & 49.9 MHz                        | T <sub>2</sub> @ 261V, 29.9MHz      | 44 A                                | 560 μJ                           | 599.8 nC                                     |
|                   | “- → 0L2” | 32.8 & 52.4 MHz                        | —                                   | —                                   | 190 μJ                           | (Q <sub>oss,T2</sub> + Q <sub>oss,T6</sub> ) |
| Inner             | “0U1 → -” | 29.7 MHz                               | T <sub>2</sub> @ 294V, 27.9MHz      | 16 A                                | 390 μJ                           | 299.9 nC                                     |
|                   | “- → 0U1” | 28.3 MHz                               | T <sub>3</sub> @ 240V, 28.3MHz      | —                                   | 320 μJ                           | (Q <sub>oss,T2</sub> )                       |

inner switches T<sub>2</sub> and T<sub>3</sub>, due to the extra inductance within loop II. According to the knowledge of switching oscillations and other commutation characteristics, the following design considerations can be recognized:

- 1) For the switching-loop design of a 3L-ANPC inverter, special efforts should be paid on minimizing the inductance of loop II, especially the PCB inductance  $L_{\sigma inv}$  exhibited in Fig. 2, to lessen the oscillation peaks exposed on the inner switches T<sub>2</sub> and T<sub>3</sub>.
- 2) For the full-mode and outer-mode operations, the EMI filters should be designed to perform sufficient attenuation for oscillation peaks at both frequency ranges (i.e., 29.9–32.8 MHz and 49.9–52.4 MHz for this work). Specific efforts should be paid on the lower frequency range of 29.4–34.3 MHz, as it features higher oscillation magnitudes. For the inner-mode operation, the EMI filter should be able to perform sufficient noise attenuation at 28.3–29.7 MHz, as significant oscillation magnitude is identified within this frequency band.
- 3) For the device-selection of inner and clamping switches (i.e., T<sub>2</sub>, T<sub>3</sub>, T<sub>5</sub>, and T<sub>6</sub>) under both the full-mode and outer-mode commutations, special attention should be paid on the value of device output capacitance  $C_{oss}$ , as well as the junction capacitance of the external diode.
- 4) In particular, the FEM simulations, e.g., the ANSYS/Q3D or Maxwell, can be a promising method for the evaluation and iteration of the design. Moreover, the technique of magnetic-field cancellation can be utilized for the mitigation of parasitic inductance [43].

## VII. CONCLUSION

This paper focuses on investigations of the multi-frequency switching-oscillations of SiC MOSFETs in 3L-ANPC inverters under three typical commutation modes (i.e., the full mode, outer mode, and inner mode). It is found that both the full mode and outer mode involve multiple loops during commutation transients, and different switching-oscillation components with various frequencies can be induced due to this switching-loop diversity. On the contrary, the inner-mode commutation features single switching oscillation at a lower frequency, since it is associated with only one switching loop. Based on the analyses of the equivalent switching circuits using FEM extracted parasitic parameters, these oscillation frequencies for the three commutation modes are identified.

Multiple switching-oscillation components are verified through DPT results obtained under the three commutation modes. For the full-mode and outer-mode commutations, various oscillation components with a frequency range from 29.9 MHz to 54.4 MHz are reported from experimental measurements. On the other hand, only one oscillation component can be identified from the DPT results of the inner-mode commutation. The oscillation frequencies derived by theory match well with these measured by experiments with reasonable errors from 0.5 MHz to 3.6 MHz.

Furthermore, other switching characteristics close related, i.e., the oscillation peaks, current overshoots, capacitive charges, and switching energies, are studied and benchmarked based on DPT results. It is obtained that the inner devices T<sub>2</sub> and T<sub>3</sub> suffer the most significant oscillation peaks for all commutation modes, as they are enclosed by loop II with a high inductance ( $L_{lp2} = 78.2$  nH). Additionally, the full mode and outer mode exhibit several similarities, both of them have excessive current overshoots, switching energies, and capacitive charges.

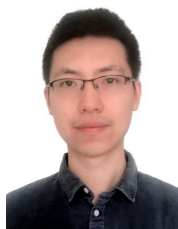
Last yet not least, several design considerations are proposed for each commutation mode. It is pointed out that special effort should be paid on minimizing the inductance of loop II, especially the PCB inductance of  $L_{\sigma inv}$ . Accordingly, balancing the inductance components contributed by loops I and II (i.e.,  $L_{lp1}$  and  $L_{lp2}$ ) helps to release the design burden of the EMI filter. Special attention should also be paid on the value of device output capacitance  $C_{oss}$  when the 3L-ANPC inverter operates under both the full mode and outer mode.

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